



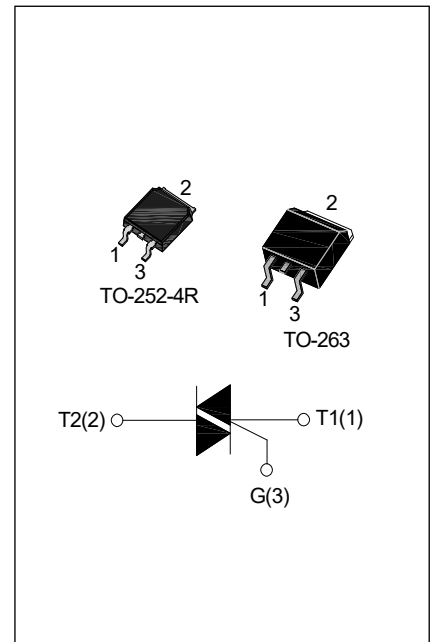
DESCRIPTION:

T06xxH series triacs of high junction temperature with high dv/dt rate with strong resistance to electromagnetic interference provide high ability to withstand the shock loading of large current. They are especially recommended for use on inductive load and high environment temperature condition.

Package TO-252 & TO-263 are RoHS compliant. (2011/65/EU)

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	6	A
V_{DRM}/V_{RRM}	600/800	V
T_{jmax}	150	°C



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-150	°C
Repetitive peak off-state voltage($T_j=25^\circ\text{C}$)	V_{DRM}	600/800	V
Repetitive peak reverse voltage($T_j=25^\circ\text{C}$)	V_{RRM}	600/800	V
RMS on-state current	TO-252-4R ($T_c=100^\circ\text{C}$)	6	A
	TO-263 ($T_c=113^\circ\text{C}$)		
Non repetitive surge peak on-state current (full cycle, $F=50\text{Hz}$)	I_{TSM}	60	A
I^2t value for fusing ($t_p=10\text{ms}$)	I^2t	21	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)	di/dt	50	$\text{A}/\mu\text{s}$
Peak gate current	I_{GM}	4	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value				Unit
				T0610H	T0620H	T0635H	T0650H	
I_{GT}	$V_D=12V R_L=33\Omega$	I - II -III	MAX	10	20	35	50	mA
V_{GT}		I - II -III	MAX	1.3				V
V_{GD}	$V_D=V_{DRM} T_j=150^\circ C$ $R_L=3.3K\Omega$	I - II -III	MIN	0.2				V
I_L	$I_G=1.2I_{GT}$	I -III	MAX	20	40	50	70	mA
		II		35	55	70	100	
I_H	$I_T=100mA$		MAX	20	30	45	60	mA
dV/dt	$V_D=2/3V_{DRM} R_{GK}=1K\Omega T_j=150^\circ C$		MIN	200	500	1000	1500	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=8.5A t_p=380\mu s$	$T_j=25^\circ C$	1.4	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ C$	5	μA
I_{RRM}		$T_j=150^\circ C$	1	mA

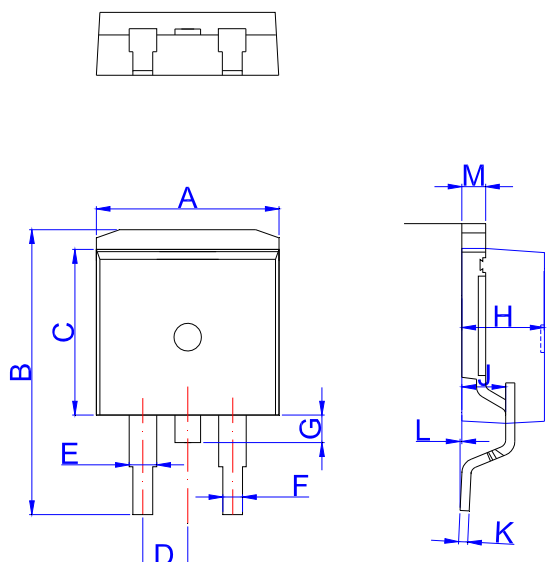
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-252-4R	1.9	$^\circ C/W$
		TO-263	1.5	
$R_{th(j-a)}$	junction to ambient	TO-252-4R	70	$^\circ C/W$
		TO-263	45	

ORDERING INFORMATION

<p>T</p> <p>Triacs</p> <p>$I_{T(RMS)}:6A$</p> <p>10: $I_{GT1-3} \leq 10mA$</p> <p>20: $I_{GT1-3} \leq 20mA$</p> <p>35: $I_{GT1-3} \leq 35mA$</p> <p>50: $I_{GT1-3} \leq 50mA$</p>	<p>06</p>	<p>20</p>	<p>H</p>	<p>-6</p> <p>6: $V_{DRM} / V_{RRM} \geq 600V$</p> <p>8: $V_{DRM} / V_{RRM} \geq 800V$</p>	<p>K</p> <p>E: TO-263</p> <p>K: TO-252-4R</p> <p>ETR: TO-263(Tape&Reel)</p> <p>KTR: TO-252-4R(Tape&Reel)</p> <p>High junction temperature</p>
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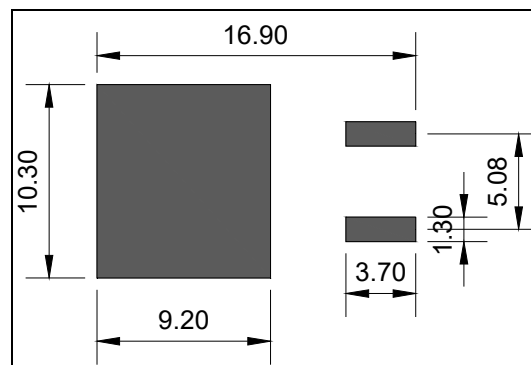
PACKAGE MECHANICAL DATA



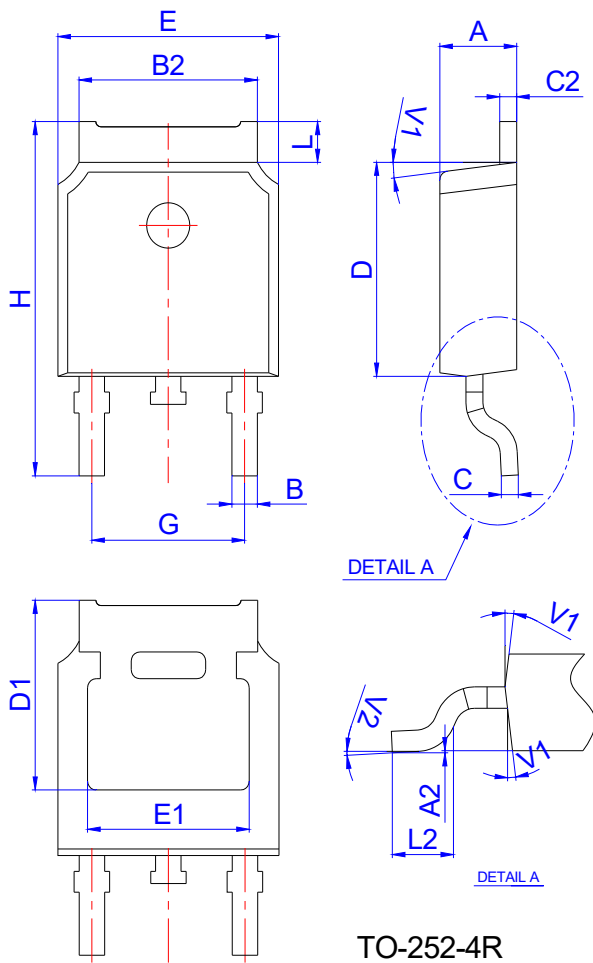
TO-263

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.4		9.6	0.37		0.378
D		2.54			0.100	
E	1.20		1.40	0.047		0.055
F	0.75		0.85	0.029		0.033
G			1.75			0.069
H	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0	0.10	0.25	0	0.004	0.010
M	1.25		1.35	0.049		0.053

FOOTPRINT-TO-263 (dimensions in mm)

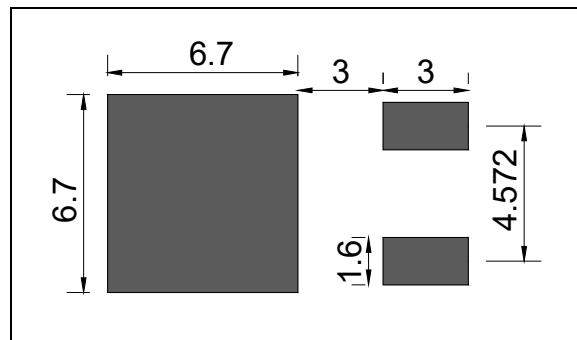


PACKAGE MECHANICAL DATA

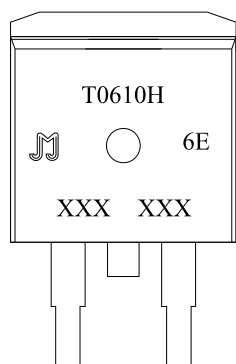


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

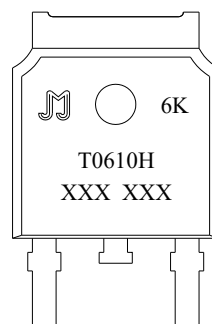
FOOTPRINT-TO-252-4R (dimensions in mm)



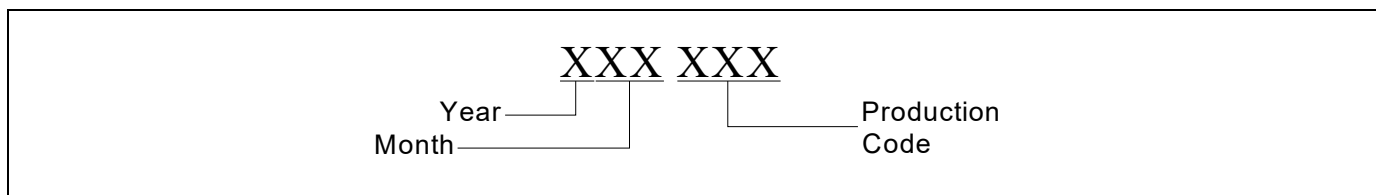
MARKING



TO-263



TO-252-4R



PACKAGE INFORMATION

PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-263	TUBE	50	1,000	6,000
TO-252-4R	TUBE	80	4,000	32,000
PACKAGE	OUTLINE	REEL (PCS)	PER CARTON (PCS)	TAPE & REEL
TO-263	TAPING	800	4,000	13 inch
TO-252-4R	TAPING	2,500	25,000	13 inch

FIG.1: Maximum power dissipation versus RMS on-state current

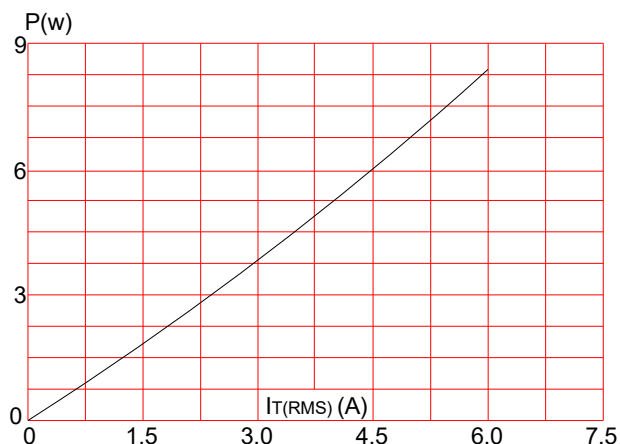


FIG.2: RMS on-state current versus case temperature

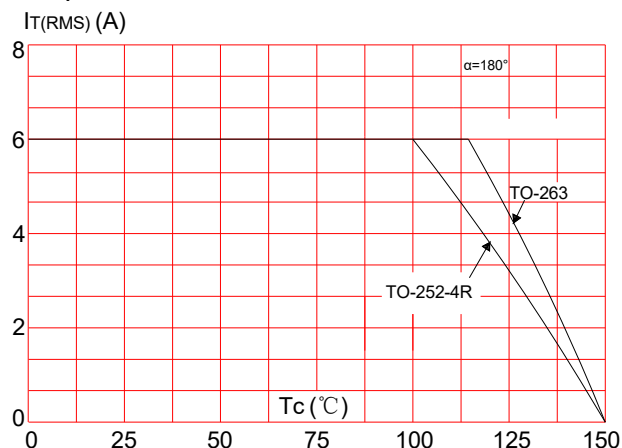


FIG.3: Surge peak on-state current versus number of cycles

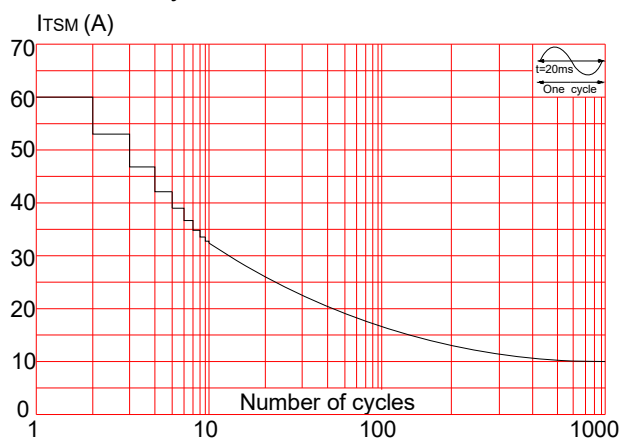


FIG.4: On-state characteristics (maximum values)

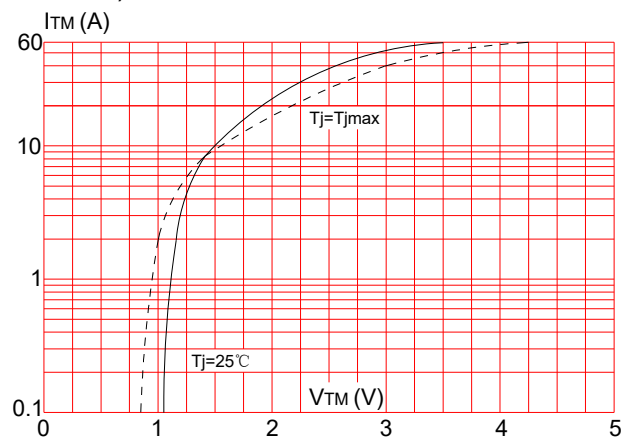


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($dI/dt < 50\text{A}/\mu\text{s}$)

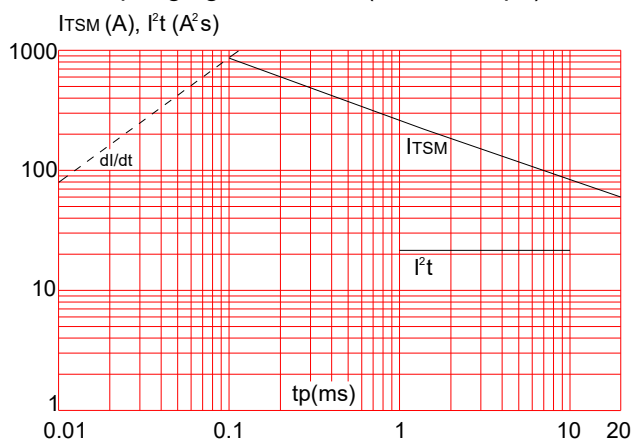
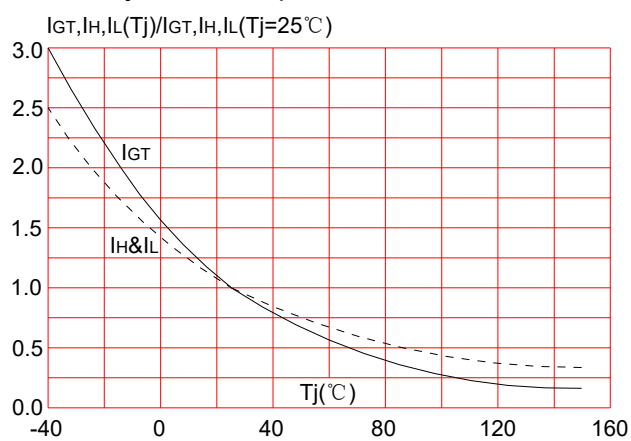
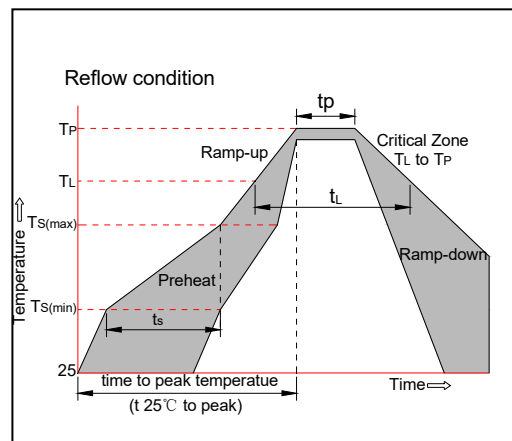


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L)to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L)(Liquidus)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		20-40secs.
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C



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